

Ki Wook Kim

List of Publications by Year in descending order

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236
papers

7,537
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50170

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docs citations

237
times ranked

7341
citing authors

#	ARTICLE	IF	CITATIONS
1	Domains of electrically induced valley polarization in two-dimensional Dirac semiconductors. <i>Physical Review B</i> , 2021, 104, .	1.1	2
2	Carrier-induced ferromagnetism in two-dimensional magnetically doped semiconductor structures. <i>Physical Review B</i> , 2021, 104, .	1.1	0
3	First-principles analysis of magnetically doped transition-metal dichalcogenides. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 025002.	1.3	6
4	Spin-transfer and fieldlike torques in antiferromagnets. <i>Physical Review B</i> , 2021, 104, .	1.1	1
5	Scalable Characterization of 2D Gallium-Intercalated Epitaxial Graphene. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 55428-55439.	4.0	5
6	Spin wave generation via localized spin-orbit torque in an antiferromagnet-topological insulator heterostructure. <i>Journal of Applied Physics</i> , 2020, 128, 043901.	1.1	0
7	Modeling of Antiferromagnetic Dynamics: A Brief Review. <i>IEEE Nanotechnology Magazine</i> , 2020, 14, 32-41.	0.9	3
8	Efficient Control of Stochastic Switching via Spin Pumping in Antiferromagnetic Structures. <i>Physical Review Applied</i> , 2020, 13, .	1.5	0
9	Optical bistability and self-opacity in magnetically doped monolayer transition metal dichalcogenides. <i>Physical Review B</i> , 2020, 102, .	1.1	0
10	Thermal fluctuations in antiferromagnetic nanostructures. <i>Journal of Magnetism and Magnetic Materials</i> , 2019, 489, 165457.	1.0	7
11	Controllable Dispersion of Domain-Wall Movement in Antiferromagnetic Thin Films at Finite Temperatures. <i>Physical Review Applied</i> , 2019, 11, .	1.5	2
12	Nanoscale ballistic diodes made of polar materials for amplification and generation of radiation in the 10 THz-range. <i>Journal of Applied Physics</i> , 2019, 126, 085708.	1.1	1
13	Electrical generation and propagation of spin waves in antiferromagnetic thin-film nanostrips. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	2
14	Creation and Destruction of Skyrmions via Electrical Modulation of Local Magnetic Anisotropy in Magnetic Thin Films. <i>Physical Review Applied</i> , 2019, 11, .	1.5	6
15	Conductance nonreciprocity on the surface of a topological insulator with magnetic electrodes. <i>Journal of Physics and Chemistry of Solids</i> , 2019, 128, 196-201.	1.9	4
16	Voltage Control of Antiferromagnetic Phases at Near-Terahertz Frequencies. <i>Physical Review Applied</i> , 2018, 9, .	1.5	19
17	Toward enhanced thermoelectric effects in Bi ₂ Te ₃ /Sb ₂ Te ₃ heterostructures. <i>Semiconductor Science and Technology</i> , 2017, 32, 035005.	1.0	10
18	Electrical switching of antiferromagnets via strongly spin-orbit coupled materials. <i>Journal of Applied Physics</i> , 2017, 121, .	1.1	14

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19	Spin pumping torque in antiferromagnets. Applied Physics Letters, 2017, 110, 192405.	1.5	7
20	Currentless reversal of Néel vector in antiferromagnets. Physical Review B, 2017, 95, .	1.1	10
21	Helical waves in easy-plane antiferromagnets. Physical Review B, 2017, 96, .	1.1	4
22	Doping induced enhanced density of states in bismuth telluride. Applied Physics Letters, 2017, 111, .	1.5	11
23	Highly anisotropic electronic transport properties of monolayer and bilayer phosphorene from first principles. Applied Physics Letters, 2016, 109, .	1.5	31
24	Atomistic modeling of phonon transport in turbostratic graphitic structures. Journal of Applied Physics, 2016, 119, .	1.1	5
25	Electrically controlled switching of antiferromagnets via proximity interaction induced by topological insulator. , 2016, , .		0
26	Bias-driven spontaneous spin-valley polarization in monolayer transition-metal dichalcogenides. Physical Review B, 2016, 93, .	1.1	8
27	Nonlinear magnetic dynamics in a nanomagnet–topological insulator heterostructure. Physical Review B, 2015, 92, .	1.1	11
28	Strain induced room temperature ferromagnetism in epitaxial magnesium oxide thin films. Journal of Applied Physics, 2015, 118, 165309.	1.1	7
29	Highly efficient conductance control in a topological insulator based magnetoelectric transistor. Journal of Applied Physics, 2015, 118, 224502.	1.1	3
30	Equally Efficient Interlayer Exciton Relaxation and Improved Absorption in Epitaxial and Nonepitaxial MoS ₂ /WS ₂ Heterostructures. Nano Letters, 2015, 15, 486-491.	4.5	337
31	Quasi-optical electron transport across a magnetically induced junction on a topological insulator surface. Journal of Applied Physics, 2014, 116, 224301.	1.1	1
32	Intrinsic transport properties of electrons and holes in monolayer transition-metal dichalcogenides. Physical Review B, 2014, 90, .	1.1	335
33	Hot-Electron Transistors for Terahertz Operation Based on Two-Dimensional Crystal Heterostructures. Physical Review Applied, 2014, 2, .	1.5	18
34	Ultrafast valley relaxation dynamics in single layer semiconductors. Proceedings of SPIE, 2014, , .	0.8	0
35	Thin-film topological insulator-ferromagnet heterostructures for terahertz detection. Applied Physics Letters, 2014, 104, .	1.5	9
36	Many-Body Effects in Valleytronics: Direct Measurement of Valley Lifetimes in Single-Layer MoS ₂ . Nano Letters, 2014, 14, 202-206.	4.5	431

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37	Spin Logic via Controlled Correlation in Nanomagnet-Dirac-Fermion Heterostructures. Physical Review Applied, 2014, 2, .	1.5	6
38	Proposal of a topological insulator based magnetoelectric transistor. , 2014, , .		0
39	Exciton valley relaxation in a single layer of WS ₂ measured by ultrafast spectroscopy. Physical Review B, 2014, 90, .	1.1	115
40	Controlling electron propagation on a topological insulator surface via proximity interactions. Physical Review B, 2014, 89, .	1.1	15
41	Thermal transport properties of metal/MoS ₂ interfaces from first principles. Journal of Applied Physics, 2014, 116, .	1.1	25
42	Voltage-driven magnetic bifurcations in nanomagnet-topological insulator heterostructures. Physical Review B, 2014, 89, .	1.1	23
43	Intrinsic electrical transport properties of monolayer silicene and MoS ₂ from first principles. Physical Review B, 2013, 87, .	1.1	380
44	Spin logic via controlled correlation in a topological insulator-nanomagnet hybrid structure. , 2013, , .		2
45	Toward stimulated interaction of surface phonon polaritons. Journal of Applied Physics, 2013, 114, 233508.	1.1	1
46	First-principles calculation of thermal transport in metal/graphene systems. Physical Review B, 2013, 87, .	1.1	56
47	Electrically controlled magnetization in ferromagnet-topological insulator heterostructures. Physical Review B, 2012, 86, .	1.1	51
48	Phonon engineering in nanostructures: Controlling interfacial thermal resistance in multilayer-graphene/dielectric heterojunctions. Applied Physics Letters, 2012, 101, 113111.	1.5	46
49	Ab initio thermal transport properties of nanostructures from density functional perturbation theory. Journal of Physics Condensed Matter, 2012, 24, 492204.	0.7	17
50	Charge transfer equilibria in ambient-exposed epitaxial graphene on (0001- $\sqrt{3}$)-SiC. Journal of Applied Physics, 2012, 111, 113706.	1.1	35
51	Electric field driven domain wall transfer in hybrid structures. , 2012, , .		0
52	THz detector based on proximity effect of topological insulator. , 2012, , .		0
53	Two dimensional crystal tunneling devices for THz operation. Applied Physics Letters, 2012, 101, .	1.5	27
54	Tunable photogalvanic effect on topological insulator surfaces via proximity interactions. Physical Review B, 2012, 86, .	1.1	21

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55	Multiple coexisting intercalation structures of sodium in epitaxial graphene-SiC interfaces. Physical Review B, 2012, 85, .	1.1	46
56	Magnetic domain wall transfer via graphene mediated electrostatic control. Applied Physics Letters, 2012, 101, 013103.	1.5	3
57	Electron transport properties of bilayer graphene. Physical Review B, 2011, 84, .	1.1	32
58	Electron transport in bulk GaN under ultrashort high-electric field transient. Semiconductor Science and Technology, 2011, 26, 105008.	1.0	4
59	Electron-phonon interactions in bilayer graphene. Physical Review B, 2011, 83, .	1.1	46
60	Weak ferromagnetism of antiferromagnetic domains in graphene with defects. Physical Review B, 2011, 84, .	1.1	8
61	Strong substrate effects of Joule heating in graphene electronics. Applied Physics Letters, 2011, 99, .	1.5	23
62	Electronic properties of the graphene/6H-SiC(0001) interface: A first-principles study. Physical Review B, 2011, 84, .	1.1	28
63	Unusual magnetoresistance in a topological insulator with a single ferromagnetic barrier. Applied Physics Letters, 2011, 98, 243112.	1.5	57
64	Generation-recombination noise in bipolar graphene. Journal of Applied Physics, 2011, 110, 044327.	1.1	5
65	Electron spin relaxation in carbon nanotubes. Physical Review B, 2010, 82, .	1.1	4
66	Influence of electron-electron scattering on transport characteristics in monolayer graphene. Applied Physics Letters, 2010, 97, .	1.5	63
67	Quasi-Coherent Thermal Emission in the Terahertz by Doped Semiconductors. IEEE Sensors Journal, 2010, 10, 443-450.	2.4	3
68	Graphene spin capacitor for magnetic field sensing. Applied Physics Letters, 2010, 97, 013106.	1.5	8
69	Surface polar phonon dominated electron transport in graphene. Applied Physics Letters, 2010, 97, .	1.5	93
70	Band Engineering and Magnetic Doping of Epitaxial Graphene on SiC (0001). Physical Review Letters, 2010, 104, 146801.	2.9	63
71	First-principles analysis of electron-phonon interactions in graphene. Physical Review B, 2010, 81, .	1.1	189
72	Large-Signal Analysis of Terahertz Generation in Submicrometer GaN Diodes. IEEE Sensors Journal, 2010, 10, 765-771.	2.4	13

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73	Thermoelectric properties of graphene nanoribbons, junctions and superlattices. Journal of Physics Condensed Matter, 2010, 22, 372202.	0.7	72
74	Electrically controlled magnetic switching based on graphene-magnet composite structures. Journal of Applied Physics, 2010, 107, 064507.	1.1	7
75	Magnetoconcentration effect in intrinsic graphene ribbons. Applied Physics Letters, 2010, 97, .	1.5	3
76	Alternate State Variables for Emerging Nanoelectronic Devices. IEEE Nanotechnology Magazine, 2009, 8, 66-75.	1.1	40
77	Terahertz generation in GaN diodes operating in pulsed regime limited by self-heating. Applied Physics Letters, 2009, 94, .	1.5	8
78	Electrically controlled magnetic memory and programmable logic based on graphene/ferromagnet hybrid structures. , 2009, , .		0
79	First-principles analysis of lattice thermal conductivity in monolayer and bilayer graphene. Physical Review B, 2009, 80, .	1.1	189
80	Nonvolatile Memory via Spin Polaron Formation. IEEE Nanotechnology Magazine, 2008, 7, 480-483.	1.1	3
81	Magnetoconductance in Bilayer Graphene Hybrid Structures for Spintronic Applications. , 2008, , .		0
82	Terahertz generation in GaN diodes in the limited space-charge accumulation mode. Journal of Applied Physics, 2008, 103, 126101.	1.1	10
83	Electrical Control of Exchange Bias Mediated by Graphene. Physical Review Letters, 2008, 101, 147206.	2.9	21
84	Electron spin relaxation via flexural phonon modes in semiconducting carbon nanotubes. Physical Review B, 2008, 77, .	1.1	11
85	Magnetic polaron for a spin memory application. Journal of Applied Physics, 2008, 104, 084306.	1.1	2
86	Terahertz emission mediated by surface plasmon polaritons in doped semiconductors with surface grating. Journal of Applied Physics, 2008, 103, 056101.	1.1	9
87	Magnetoconductance in bilayer graphene via ferromagnet proximity effects. Physical Review B, 2008, 77, .	1.1	25
88	Elastic spin-relaxation processes in semiconductor quantum dots. Physical Review B, 2007, 75, .	1.1	28
89	Quasimonochromatic emission spectra in the near field by polar semiconductor thermal sources. Applied Physics Letters, 2007, 90, 113106.	1.5	4
90	Negative small-signal impedance of nanoscale GaN diodes in the terahertz frequency regime. Applied Physics Letters, 2007, 90, 142117.	1.5	7

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91	Electron spin relaxation in semiconducting carbon nanotubes: The role of hyperfine interaction. Physical Review B, 2007, 75, .	1.1	15
92	Imaging properties of a metallic photonic crystal. Journal of Applied Physics, 2007, 101, 113105.	1.1	3
93	A quantum dot memory cell based on spin polaron formation. , 2007, , .		0
94	Spin field effect transistor with a graphene channel. Applied Physics Letters, 2007, 91, 153105.	1.5	169
95	Electrical Manipulation of Nonvolatile Spin Cell Based on Diluted Magnetic Semiconductor Quantum Dots. IEEE Transactions on Electron Devices, 2007, 54, 1032-1039.	1.6	1
96	Realization of tunable photonic crystals based on the metal insulator transition of VO ₂ . , 2006, 6128, 41.		0
97	Emerging memory devices. IEEE Circuits and Devices: the Magazine of Electronic and Photonic Systems, 2006, 22, 12-21.	0.8	40
98	Subpicosecond Raman studies of electric-field-induced optical phonon instability in an In _{0.53} Ga _{0.47} As-based semiconductor nanostructure. Journal of Physics Condensed Matter, 2006, 18, 7961-7974.	0.7	6
99	Optical phonon instability induced by high-speed electron transport in nanoscale semiconductor structures. Physical Review B, 2006, 73, .	1.1	1
100	Tunable waveguiding in electrically programmable VO ₂ -based photonic crystals. Journal of Applied Physics, 2006, 99, 113106.	1.1	8
101	High-speed and high-frequency electron effects in nitride semiconductors for terahertz applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2569-2572.	0.8	2
102	Exchange Effects on Electronic States in QWs with e-h Plasma in an Electric Field. AIP Conference Proceedings, 2005, , .	0.3	0
103	Nitride-based two-terminal oscillators operating in the THz regime. , 2005, , .		1
104	Analysis of the $\hat{\Gamma}^m(X) \hat{\Gamma}^n L$ intervalley mixing in group-IV heterostructures. AIP Conference Proceedings, 2005, , .	0.3	0
105	Pekar Mechanism of Electron-Phonon Interaction in Nanostructures. AIP Conference Proceedings, 2005, , .	0.3	0
106	Bistability in a magnetic and nonmagnetic double-quantum-well structure mediated by the magnetic phase transition. Applied Physics Letters, 2005, 86, 073107.	1.5	5
107	Prohibition of equilibrium spin currents in multiterminal ballistic devices. Physical Review B, 2005, 71, .	1.1	47
108	Nonvolatile bistability effect based on the electrically controlled phase transition in scaled magnetic semiconductor nanostructures. Physical Review B, 2005, 72, .	1.1	5

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109	Terahertz generation in submicron GaN diodes within the limited space-charge accumulation regime. Journal of Applied Physics, 2005, 98, 064507.	1.1	38
110	Electrically programmable photonic crystal slab based on the metal-insulator transition in VO ₂ . Journal of Applied Physics, 2005, 97, 106102.	1.1	26
111	Coulombic effects of electron-hole plasma in nitride-based nanostructures. Journal of Applied Physics, 2005, 98, 063711.	1.1	3
112	Spin relaxation of two-dimensional holes in strained asymmetric SiGe quantum wells. Physical Review B, 2005, 71, .	1.1	9
113	Electron-phonon interaction via the Pekar mechanism in nanostructures. Physical Review B, 2005, 71, .	1.1	12
114	L-valley electrons in SiGe heterostructures: highly anisotropic and tunable Zeeman and Rashba-like spin splittings. AIP Conference Proceedings, 2005, , .	0.3	0
115	Phonon-Mediated Electron-Spin Phase Diffusion in a Quantum Dot. Physical Review Letters, 2004, 92, 026601.	2.9	67
116	Resonance-like electrical control of electron spin for microwave measurement. Applied Physics Letters, 2004, 85, 428-430.	1.5	0
117	Spin polaron and bistability in ferromagnetic semiconductor quantum structures. Physical Review B, 2004, 70, .	1.1	3
118	Tunable terahertz-frequency resonances and negative dynamic conductivity of two-dimensional electrons in group-III nitrides. Journal of Applied Physics, 2004, 96, 6488-6491.	1.1	31
119	Envelope-function analysis of wurtzite InGaN/GaN quantum well light emitting diodes. Journal of Applied Physics, 2004, 96, 723-728.	1.1	9
120	Low-field electron runaway and spontaneous formation of two-beam velocity distribution in polar semiconductors. Physical Review B, 2004, 69, .	1.1	2
121	Phase-plane analysis and classification of transient regimes for high-field electron transport in nitride semiconductors. Journal of Applied Physics, 2004, 96, 6492-6503.	1.1	9
122	High-frequency small-signal conductivity of hot electrons in nitride semiconductors. Applied Physics Letters, 2004, 84, 3630-3632.	1.5	16
123	Correlation of phonon decay with localized electron spin-phase diffusion. Physical Review B, 2004, 70, .	1.1	3
124	QUASI-BALLISTIC AND OVERSHOOT TRANSPORT IN GROUP III-NITRIDES. International Journal of High Speed Electronics and Systems, 2004, 14, 127-154.	0.3	3
125	Design of white light-emitting diodes using InGaN/AlInGaN quantum-well structures. Applied Physics Letters, 2004, 84, 672-674.	1.5	42
126	QUASI-BALLISTIC AND OVERSHOOT TRANSPORT IN GROUP III-NITRIDES. Selected Topics in Electronics and Systems, 2004, , 127-154.	0.2	0

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127	Effect of an external magnetic field on electron-spin dephasing induced by hyperfine interaction in quantum dots. <i>Physical Review B</i> , 2003, 67, .	1.1	54
128	Spin-lattice relaxation in Si quantum dots. <i>Physical Review B</i> , 2003, 68, .	1.1	25
129	T-shaped spin filter with a ring resonator. <i>Journal of Applied Physics</i> , 2003, 94, 4001-4005.	1.1	95
130	Nonlinear regimes of coherent optical phonon generation in quantum wells under electric current pumping. <i>Physical Review B</i> , 2003, 68, .	1.1	5
131	Electron spin relaxation under drift in GaAs. <i>Applied Physics Letters</i> , 2003, 82, 3686-3688.	1.5	37
132	Observation of optical phonon instability induced by drifting electrons in semiconductor nanostructures. <i>Applied Physics Letters</i> , 2003, 82, 1968-1970.	1.5	21
133	Streaming distribution of two-dimensional electrons in III-N heterostructures for electrically pumped terahertz generation. <i>Applied Physics Letters</i> , 2003, 82, 2643-2645.	1.5	20
134	Manipulating the L-valley electron factor in Si-Ge heterostructures. <i>Physical Review B</i> , 2003, 68, .	1.1	14
135	Observation of field-induced optical phonon amplification in semiconductor nanostructures. , 2003, , .		0
136	Spin relaxation of conduction electrons in bulk III-V semiconductors. <i>Physical Review B</i> , 2002, 66, .	1.1	135
137	Designing a heterostructure for the quantum receiver. <i>Applied Physics Letters</i> , 2002, 80, 2857-2859.	1.5	12
138	Transmission of longitudinal optical phonons through a barrier in uniaxial crystals. <i>Physical Review B</i> , 2002, 65, .	1.1	8
139	Generation of high-frequency coherent acoustic phonons in superlattices under hopping transport. I. Linear theory of phonon instability. <i>Physical Review B</i> , 2002, 65, .	1.1	25
140	Laterally doped heterostructures for III-V lasing devices. <i>Applied Physics Letters</i> , 2002, 81, 4616-4618.	1.5	7
141	Generation of high-frequency coherent acoustic phonons in superlattices under hopping transport. II. Steady-state phonon population and electric current in generation regime. <i>Physical Review B</i> , 2002, 65, .	1.1	7
142	Spin-phase relaxation of two-dimensional holes localized in a fluctuating potential. <i>Physical Review B</i> , 2002, 66, .	1.1	8
143	HIGH-FIELD ELECTRON TRANSPORT CONTROLLED BY OPTICAL PHONON EMISSION IN NITRIDES. <i>International Journal of High Speed Electronics and Systems</i> , 2002, 12, 1057-1081.	0.3	4
144	Cerenkov generation of confined acoustic and optical phonons in quantum wells. , 2002, 4643, 77.		0

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145	Confinement and amplification of acoustic waves in cubic heterostructures. <i>Physical Review B</i> , 2002, 65, .	1.1	0
146	Hot electrons in group-III nitrides at moderate electric fields. <i>Applied Physics Letters</i> , 2002, 80, 2317-2319.	1.5	24
147	Amplification of transverse acoustic phonons in quantum well heterostructures with piezoelectric interaction. <i>Journal of Applied Physics</i> , 2001, 90, 3934-3941.	1.1	9
148	T-shaped ballistic spin filter. <i>Applied Physics Letters</i> , 2001, 78, 775-777.	1.5	150
149	Generation of coherent confined LO phonons under the drift of two-dimensional electrons. <i>Physical Review B</i> , 2001, 63, .	1.1	14
150	Continuum model of optical phonons in a nanotube. <i>Superlattices and Microstructures</i> , 2001, 29, 405-409.	1.4	30
151	Applicability of the Fermi golden rule and the possibility of low-field runaway transport in nitrides. <i>Journal of Physics Condensed Matter</i> , 2001, 13, 6233-6246.	0.7	13
152	Electron g factor engineering in III-V semiconductors for quantum communications. <i>Electronics Letters</i> , 2001, 37, 464.	0.5	100
153	Runaway effects in nanoscale group-III nitride semiconductor structures. <i>Physical Review B</i> , 2001, 64, .	1.1	8
154	In-plane light-hole factor in strained cubic heterostructures. <i>Physical Review B</i> , 2001, 64, .	1.1	27
155	Quantized vibrational modes of nanospheres and nanotubes in the elastic continuum model. <i>Journal of Applied Physics</i> , 2001, 89, 5107-5111.	1.1	70
156	Scalable solid-state quantum computer based on quantum dot pillar structures. <i>Physical Review B</i> , 2000, 61, 7526-7535.	1.1	30
157	Thermal conductivity of Si/Ge superlattices: A realistic model with a diatomic unit cell. <i>Physical Review B</i> , 2000, 62, 6896-6899.	1.1	53
158	Cerenkov generation of high-frequency confined acoustic phonons in quantum wells. <i>Applied Physics Letters</i> , 2000, 76, 1869-1871.	1.5	20
159	NMR quantum computation with indirectly coupled gates. <i>Physical Review A</i> , 2000, 62, .	1.0	43
160	Progressive suppression of spin relaxation in two-dimensional channels of finite width. <i>Physical Review B</i> , 2000, 61, 13115-13120.	1.1	150
161	Energy-dependent electron scattering via interaction with optical phonons in wurtzite crystals and quantum wells. <i>Physical Review B</i> , 2000, 61, 2034-2040.	1.1	53
162	Generation and amplification of sub-THz coherent acoustic phonons under the drift of two-dimensional electrons. <i>Physical Review B</i> , 2000, 62, 7459-7469.	1.1	43

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163	Coherent optical phonon generation by the electric current in quantum wells. Applied Physics Letters, 2000, 77, 4178-4180.	1.5	14
164	Quantum computing with complex instruction sets. Physical Review A, 1999, 59, 1098-1101.	1.0	22
165	Computing carrier interactions with confined and excluded phonons in nanostructures of complex geometries. Physical Review B, 1999, 59, 10212-10216.	1.1	5
166	Optically driven quantum-dot quantum computer. Physical Review A, 1999, 60, 4146-4149.	1.0	21
167	Zeeman Effect in Wurtzite-Based and Strained Cubic Heterostructures. Physica Status Solidi (B): Basic Research, 1999, 215, 235-239.	0.7	12
168	Dispersion of polar optical phonons in wurtzite quantum wells. Physical Review B, 1999, 59, 5013-5020.	1.1	154
169	Calculational approach for the structure of electron and hole levels in quantum dots of varying shape. Physical Review B, 1999, 60, 7748-7751.	1.1	5
170	Temperature dependence of impact ionization coefficients in p-Si. Journal of Applied Physics, 1998, 83, 4988-4990.	1.1	4
171	Long-wavelength optical phonons in ternary nitride-based crystals. Physical Review B, 1998, 58, 15283-15287.	1.1	64
172	Optical-phonon confinement and scattering in wurtzite heterostructures. Physical Review B, 1998, 58, 4860-4865.	1.1	146
173	Renormalization of acoustic phonon spectra and rudiments of the Peierls transition in free-standing quantum wires. Physical Review B, 1998, 58, 16360-16368.	1.1	8
174	OPTOELECTRONIC PROPERTIES OF STRAINED WURTZITE GaN QUANTUM-WELL LASERS. International Journal of High Speed Electronics and Systems, 1998, 09, 1189-1209.	0.3	0
175	Electrophonon resonance in cylindrical quantum wires. Physical Review B, 1998, 58, 3580-3583.	1.1	20
176	Deutsch-Jozsa algorithm as a test of quantum computation. Physical Review A, 1998, 58, R1633-R1636.	1.0	104
177	Phonon assisted intersubband transitions in step quantum well structures. Journal of Applied Physics, 1998, 84, 2155-2164.	1.1	46
178	RECENT DEVELOPMENTS ON ELECTRON-PHONON INTERACTIONS IN STRUCTURES FOR ELECTRONIC AND OPTOELECTRONIC DEVICES. Selected Topics in Electronics and Systems, 1998, , 281-312.	0.2	0
179	Near-surface electrons and acoustic phonons: Energy and momentum relaxation. Physical Review B, 1997, 56, 15770-15781.	1.1	10
180	Carrier capture in pseudomorphically strained wurtzite GaN quantum-well lasers. Applied Physics Letters, 1997, 71, 820-822.	1.5	9

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181	Strain effects on optical gain in wurtzite GaN. Journal of Applied Physics, 1997, 82, 386-391.	1.1	27
182	Transient ballistic transport in GaN. Journal of Applied Physics, 1997, 81, 2901-2903.	1.1	16
183	Hole scattering and optical transitions in wide-band-gap nitrides: Wurtzite and zinc-blende structures. Physical Review B, 1997, 55, 4360-4375.	1.1	43
184	Anisotropic hole scattering in hexagonal GaN. Semiconductor Science and Technology, 1997, 12, 280-283.	1.0	8
185	Electron-phonon scattering in wurtzite crystals. Physical Review B, 1997, 56, 997-1000.	1.1	121
186	Transfer matrix method for interface optical-phonon modes in multiple-interface heterostructure systems. Journal of Applied Physics, 1997, 82, 3363-3367.	1.1	82
187	Electron interaction with confined acoustic phonons in cylindrical quantum wires via deformation potential. Journal of Applied Physics, 1996, 80, 2815-2822.	1.1	19
188	Strain effects on valence band structure in wurtzite GaN quantum wells. Applied Physics Letters, 1996, 69, 2504-2506.	1.5	31
189	Optical properties of ultrathin GaAs/AlAs quantum well structures with an electric field. Journal of Applied Physics, 1996, 79, 8675-8681.	1.1	2
190	Elastic vibrations of microtubules in a fluid. Physical Review E, 1996, 53, 1003-1010.	0.8	107
191	Envelope-function formalism for valence bands in wurtzite quantum wells. Physical Review B, 1996, 53, 1997-2009.	1.1	68
192	Dynamics of cytoskeletal filaments. Physical Review E, 1996, 54, 1816-1823.	0.8	13
193	Carrier capture in quantum well embedded quantum wire structures. Applied Physics Letters, 1996, 69, 360-362.	1.5	4
194	Tight-binding study of optical properties in short-period In _{0.53} Ga _{0.47} As/InP superlattices. Physical Review B, 1996, 53, 6939-6942.	1.1	2
195	Acoustic phonon quantization in buried waveguides and resonators. Journal of Physics Condensed Matter, 1996, 8, 2143-2151.	0.7	33
196	Carrier capture in cylindrical quantum wires. Applied Physics Letters, 1995, 67, 3480-3482.	1.5	9
197	Ballistic propagation of interface optical phonons. Physical Review B, 1995, 51, 9863-9866.	1.1	1
198	Theoretical study of electron transport in gallium nitride. Journal of Applied Physics, 1995, 77, 2834-2836.	1.1	93

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